Ref. No. : BBHKN-20-00010 Date : August 28, 2020

<Drafted by : Uchino>

CHANGE NOTICE for DOUBLE MOLDED COUPLER

Change of transistor chip

We would appreciate your continuous patronage of our semiconductor products. With regards to our Photo coupler product which is used at your company, please be noticed the following change is planned.

Your guidance and continued support would be highly appreciated.

1. Products to be affected (including specific products)

TLP185(E)	TLP184(E)	TLP290(E)	TLP290-4(E)
TLP291(E)	TLP291-4(E)	TLP385(E)	TLP620M(E)
TLP182(E)	TLP183(E)	TLP292(E)	TLP292-4(E)
TLP293(E)	TLP293-4(E)	TLP383(E)	_

^{*}Double molded couplers with transistor output are to be affected.

2. Description of change: The following changes are planed

No.	Content of change and reason	Before change No Equi-potential Ring	After change Add Equi-potential Ring	Products to be affected
1)	Change of photo detecting chip TLP185 (Representative)			TLP184(E), TLP290(E) TLP290-4(E) TLP291(E) TLP291-4(E), TLP385(E) TLP620(E)
2)	Change of photo detecting chip TLP293 (Representative)			TLP182(E), TLP183(E) TLP292(E), TLP292-4(E) TLP293-4(E), TLP383(E)

3. Purpose of change: Consolidation of photo detecting chips.

4. Product characteristics:

Since it is a consolidation of photo detecting chips, no change is expected in the product design and process. The change does not affect the initial characteristics and reliability before/after the change.

5. Effective date of the change:

We plan this change to be effective from the production of November 2020.

6. Request :

It would be appreciated if you could notify through our Sales representative in case of any inconvenience relating to this change. **Notification due date : October 16, 2020**

If Toshiba does not receive any reply with regards to this change by the due above date, it will be assumed that the change is acceptable.

Sincerely yours,

H. Matsuo / Manager Quality Planning Group

H. Matsuro

Quality Assurance Department

Buzen Toshiba Electronics Corporation

Change Notice for Toshiba Product

Change of photo detecting chip for General-use Tr Coupler

TOSHIBA

Toshiba Electronic Devices & Storage Corporation August 28, 2020

Background and affected product

1 Description of the change: Consolidate a few kinds of photo detecting Tr chips

②Purpose of the change : Reduce the control steps by consolidating chips

③Affected product : All General-use Double Molded Coupler introducing photo detecting Tr chips

■ Affected product (Photo detecting Tr chip for Photo coupler)

Affected series	Affected product	Description of the change
TLP185/293 Series	Refer to the attachment for the details	Consolidate photo detecting Tr chips

Change point in the process

Main change in the consolidation of Tr chips

5M1E		(Kaga)Manufa	cturing line	
		Before change	After change	
Design / Pattern		-	With EQR	
Man(人)		No chai	nge	
Machine(装置)			ge	
Material (原材料)		No change		
Method (方法)		No char	nge	
Measurement (測定)		No change		
Environment (環境)	Cleanliness level	No change		
, ,	System	No chai	nge	

QC Process Chart (Photo-Tr)

Before change

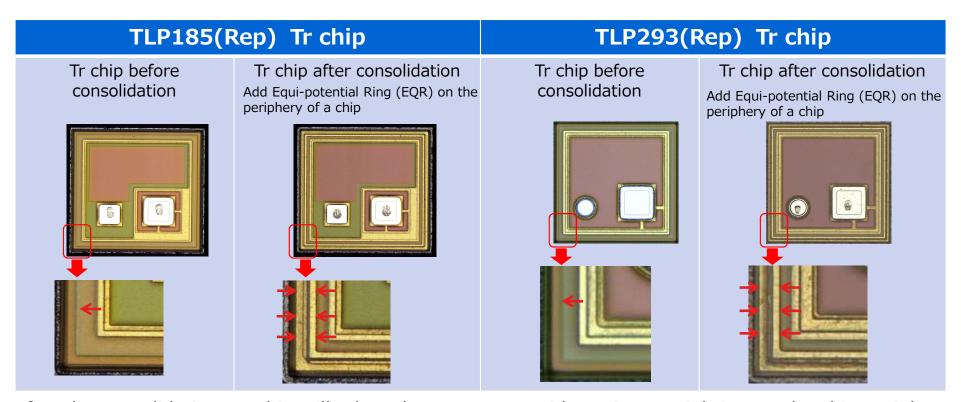
#	製造工程	* T T D	* TP 15 CF
フローチャート	工 程 名	管理項目	管理頻度
Y	ウェーハ受入		
O -0	酸化	膜厚	1回/チャージ
0 -0	ベース形成	温度	常時モニタ
<u></u>	エミッタ形成	温度	常時モニタ
<u>~</u> □	コンタクト開孔	外観	1回/ロット
	メタル形成	膜厚	1回/ロット
	パッシベーション形成	外観	1回/ロット
	特性検査	電気的特性	
	ラッピング	ウェーハ厚	1回/ロット
\ \times \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	裏面メタル形成		
\	ダイシング		
	外観検査		
\downarrow	出荷		
工程図示記号	▽: 貯蔵 ○: 加工 □:全数	 検査 □: 抜取検査 □Δ:	 特殊検査 ○─□:チェック

After change

#	製造工程	* '' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	姓丽
フローチャート	工 程 名	管理項目	管理頻度
Y	ウェーハ受入		
O-	酸化	膜厚	1回/チャージ
	ベース形成	温度	常時モニタ
	エミッタ形成	温度	常時モニタ
<u></u>	コンタクト開孔	外観	1回/ロット
Ŏ	メタル形成	膜厚	1回/ロット
	パッシベーション形成	外観	1回/ロット
	特性検査	電気的特性	
	ラッピング	ウェーハ厚	1回/ロット
j j	裏面メタル形成		
 	ダイシング		
	外観検査		
\downarrow	出荷		
工程図示記号	▽: 貯蔵 ○: 加工 □:全数	検査 ☑: 抜取検査 ☑△:	 特殊検査 ○─□:チェック

No change is planned in the QC Process Chart.

Change Point: Tr chip with EQR



After the consolidation, Tr chip will adopt the AL pattern with Equi-potential ring on the chip periphery. No difference is expected in the chip size, basic design, and characteristics.

Consequently, no change point will arise in the characteristics and reliability has a photo coupler.

Product using the same chip as TLP185: TLP184/TLP290/TLP290-4/TLP291/TP291-4/TLP385/TLP620M Product using the same chip as TLP293: TLP182/TLP183/TLP292/TLP292-4/TLP293-4/TLP383

Confidential

Product evaluation

- 1) Characteristics test
 - Comparison of the electrical characteristics
 - * Since the change point exists in the photo detector side, the photo detecting and coupling characteristics were compared.
- 2) Electrostatic discharge resistance
 - · ESD
- 3) Reliability test
 - •Selected TLP185/TLP293 as the representative, and conducted the tests.

No.	Test item	Test condition	Test time	Quantity
1	High temperature continuous operation	Ta=85℃, Voltage/Current = Operation Max	1000 h	60
2	High temperature storage	Ta=125℃	1000 h	60
3	High temperature, High humidity biased	Ta=85℃, RH=85%, Voltage= Operation Max	1000 h	60
4	Pressure cooker	Ta=121℃, 0.203MPa(No-condensation)	96 h	60
5	Temperature cycling	-55°C(30min)~125°C(30min)	300 cycle	60

^{*} Pre-treatment (saturated absorption + reflow) was conducted for all test items

- 4) Process vefication
 - Process capability (element characteristics item)

Confidential

Initial characteristics distribution (Process capability)

Before change n=50After change n=50

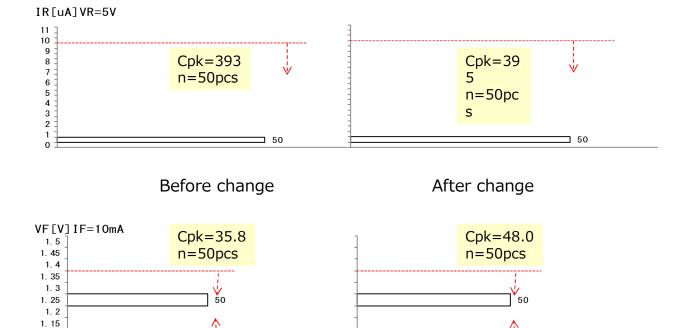
TLP185 Initial characteristics data : Standard condition $@Ta=25(^{\circ}C)$

Item	Toot condition	Specification (TD)		Before change		After change			
Item	Item Test condition	Min.	Тур.	Max.	Unit	Ave.	Cpk	Ave.	Cpk
IR	VR=5V	1	_	10	μΑ	0.01	393	0.01	395
VF	IF=10mA	1.1	1.25	1.4	V	1.22	35.8	1.22	48.0
VCEO	IC=0.5mA	80	_	_	V	149	49.1	144	52.3
VECO	IE=0.1mA	7	_	_	V	9.77	31.4	9.90	36.8
Iceo	VCE=48V	I	0.01	0.08	μΑ	0.01	3.54	0.01	3.57
IC/IF(1)	IF=5mA VCE=5 V	50	_	400	%	314	2.95	312	5.97
IC/IF(sat)	IF=1mA VCE=0.4 V	30	_	_	%	186	8.88	184	17.3
VCE(sat)	IC=2.4mA IF=8mA	_	_	0.3	V	0.133	23.6	0.145	26.4
IC(off)	VF=0.7 V VCE=48 V	_	1	10	μΑ	0.03	135	0.02	151

Changed product has sufficient process capability

Before change

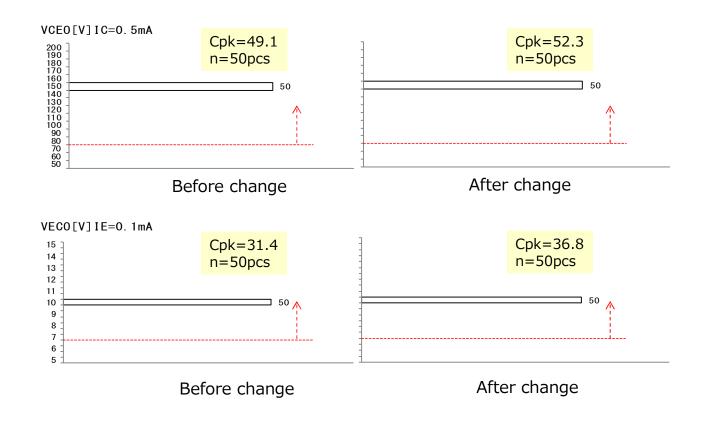
Part No.: TLP185



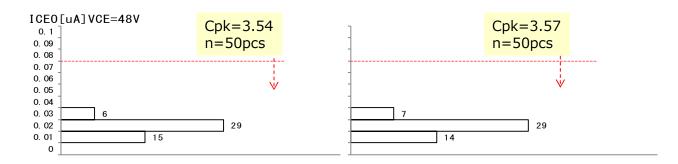
After change

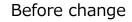
Confidential

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Part No.: TLP185

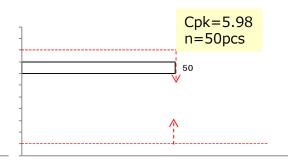




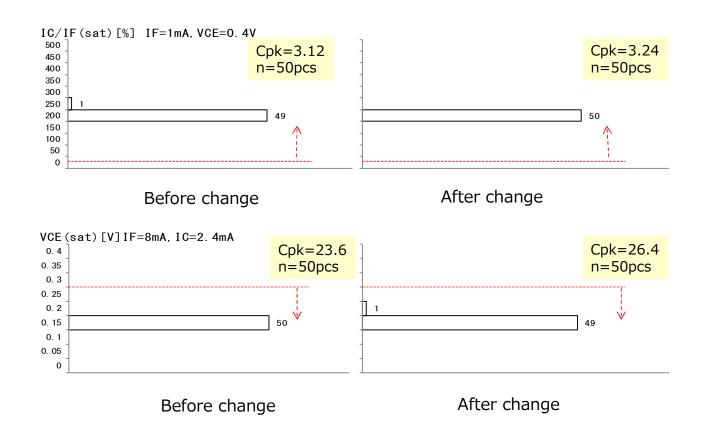
Cpk=2.95 500 450 400 350 300 250 200 100 50 0

Before change

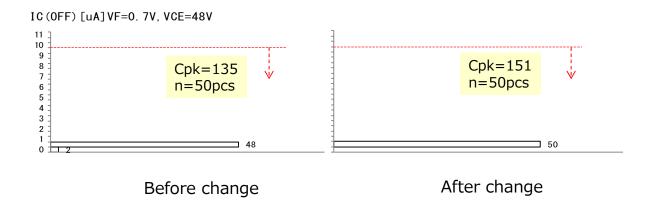
After change



After change



Part No.: TLP185



Comparing to the conventional product, process capability of changed product is equivalent or more.

Application test data (ESD test)

Part No.: TLP185

Test result: Machine mode (MM)

Part No.	Test result(±200V): Failed Q'ty / Tested Q'ty			
TLP185	Before change 0/10 pcs			
	After change 0/10 pcs			

Test condition : C=200pF, R= 0Ω , Applying once

Changed product demonstrated sufficient performance.

Test result: Human Body Model (HBM)

Part No.	Test result(±2006 Failed Q'ty / Test			
TLP185	Before change 0/10 pcs			
	After change 0/10 pcs			

Test condition : C= 100pF, R=1.5 k Ω , Applying once

Changed product demonstrated sufficient performance.

Test result : Charged Device Model (CDM)

Part No.	Test result(±500V): Failed Q'ty / Tested Q'ty			
TLP185	Before change 0/10 pcs			
	After change 0/10 pcs			

JEITA test condition: Applying once

Changed product demonstrated sufficient performance.

Reliability test result

Part No.: TLP185 (Representative)

	Test item		Judgement (Failed Q'ty / Tested Q'ty)			
No.		Test condition	Test time	Before change	After change	
1	Continuous operation	Ta=110℃,IF=20mA,Po=23mW	1000 h	0/60 pcs	0/60 pcs	
2	High temperature storage	Ta=125℃	1000 h	0/60 pcs	0/60 pcs	
3	High temperature High humidity Continuous operation	Ta=85℃, RH=85%, VCE=80V	1000 h	0/60 pcs	0/60 pcs	
4	Pressure cooker	Ta=121℃, 203kPa (No-condensation)	96 h	0/60 pcs	0/60 pcs	
5	Temperature cycling	-55°C(30min)~125°C(30min)	300 cycle	0/60 pcs	0/60 pcs	

^{*} Pre-treatment (saturated absorption + reflow) was conducted for all test items

No failure occurred in each test item. We therefore conclude that changed product has equivalent level with the conventional product.

Initial characteristics distribution (Process capability)

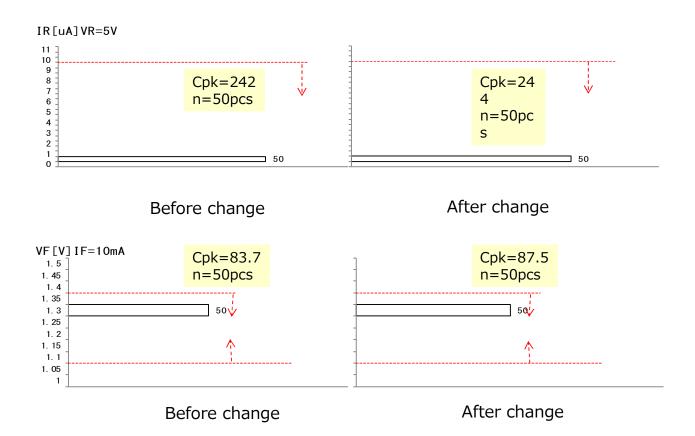
Before change n=50pcsAfter change n=50pcs

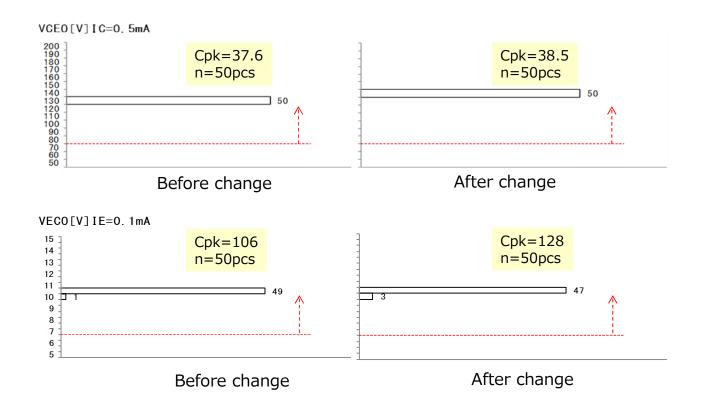
TLP293 Initial characteristic data: Standard condition

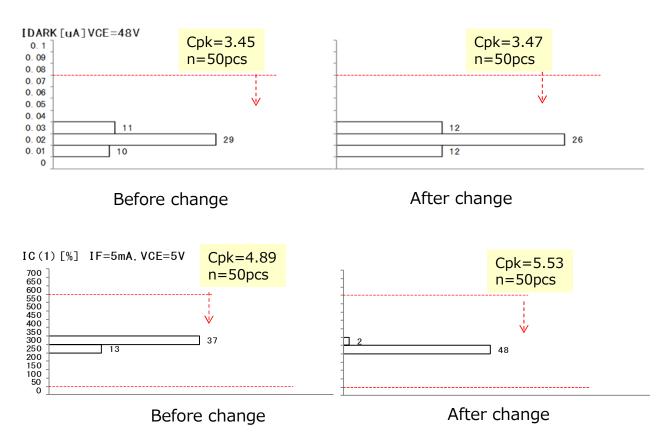
@Ta=25(°C)

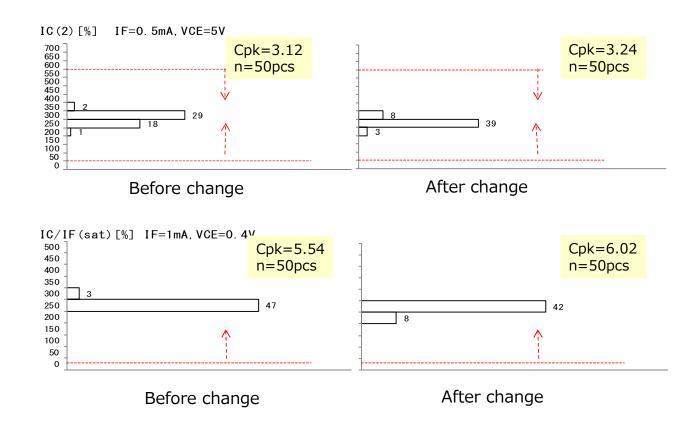
Item	Test condition	Specification (TD)			Before change		After change		
		Min.	Тур.	Max.	Unit	Ave.	Cpk	Ave.	Cpk
IR	VR=5V	_	_	10	μΑ	0.03	242	0.03	244
VF	IF=10mA	1.1	1.25	1.4	V	1.27	63.7	1.28	87.5
VCEO	IC=0.5mA	80	_	_	V	128	37.6	135	38.5
VECO	IE=0.1mA	7	_	_	V	10.0	106	10.0	128
IDARK	VCE=48V	_	0.01	0.08	μΑ	0.02	3.45	0.01	3.47
IC/IF(1)	IF=5mA VCE=5 V	50	_	600	%	259	4.89	230	5.53
IC/IF(2)	IF=0.5mA VCE=5V	50	_	600	%	256	3.12	230	3.24
IC/IF(sat)	IF=1mA VCE=0.4 V	30	_	_	%	233	5.54	212	6.02
VCE(sat)	IC=2.4mA IF=8mA	_	_	0.3	V	0.125	25.4	0.13	27.1
IC(off)	VF=0.7 V VCE=48 V	_	_	10	μΑ	0.08	135	0.08	145

Changed product has sufficient process capability

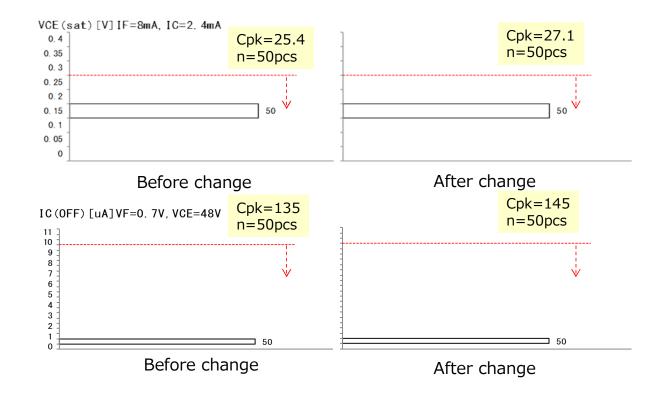








Part No.: TLP293



Comparing to the conventional product, process capability of changed products is equivalent or more.

Application test data (ESD test)

Part No.: TLP293

Test result: Machine mode (MM)

Part No.	Test result(±200 Failed Q'ty / Test	V): ed Q'ty
TLP29 3	Before change	0/10 pcs
	After change	0/10 pcs

Test condition : C=200pF, R= 0Ω , Applying once

Changed product demonstrated sufficient performance.

Test result: Human Body Model (HBM)

Part No.

Test result(±2000V):
Failed Q'ty / Tested Q'ty

TLP293

Before change 0/10 pcs

After change 0/10 pcs

Test condition : C= 100pF, R=1.5 k Ω , Applying once

Changed product demonstrated sufficient performance.

Test result: Charged Device Model (CDM) JEITA test condition: Applying once

Part No.	Test result(±500V): Failed Q'ty / Tested Q'th				
TLP293	Before change	0/10 pcs			
	After change	0/10 pcs			

Changed product demonstrated sufficient performance.

Reliability test result

Part No.: TLP293 (Representative)

			Judgement (Failed Q'ty / Tested Q'ty)			
No.	Test item	Test condition	Test time	Before change	After change	
1	Continuous operation	Ta=125℃,IF=12mA,Po=14mW	1000 h	0/60 pcs	0/60 pcs	
2	High temperature storage	Ta=125℃	1000 h	0/60 pcs	0/60 pcs	
3	High temperature High humidity Continuous operation	Ta=85℃, RH=85%, VCE=80V	1000 h	0/60 pcs	0/60 pcs	
4	Pressure cooker	Ta=121℃, 203kPa (No-condensation)	96 h	0/60 pcs	0/60 pcs	
5	Temperature cycling	-55°C(30 min)~125°C(30 min)	300 cycle	0/60 pcs	0/60 pcs	

^{*} Pre-treatment (saturated absorption + reflow) was conducted for all test items

No failure occurred in each test item. We therefore conclude that changed product has equivalent level with the conventional product.

Conclusion

As explained in the report, we have obtained the equivalent results at each test before and after the change.

Consequently, we would like to ask your consideration for the approval of consolidation of Tr chip.

Your understanding and corporation would be highly appreciated.

TOSHIBA